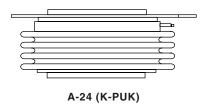


## Vishay High Power Products

## Phase Control Thyristors (Stud Version), 1650 A



PRODUCT SUMMARY			
I <sub>T(AV)</sub>	1650 A		

#### **FEATURES**

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level

### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		1650	А			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
1		3080	А			
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C			
I <sub>TSM</sub>	50 Hz	30 500	٨			
	60 Hz	32 000	Α			
121	50 Hz	4651	kA <sup>2</sup> s			
l <sup>2</sup> t	60 Hz	4250	KA-S			
V <sub>DRM</sub> /V <sub>RRM</sub>		1200 to 2000	V			
t <sub>q</sub>	Typical	200	μѕ			
T <sub>J</sub>		- 40 to 125	°C			

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA				
	12	1200	1300					
	14	1400	1500					
ST1200CK	16	1600	1700	100				
	18	1800	1900					
	20	2000	2100					

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## ST1200C..KP Series

# Vishay High Power Products

# Phase Control Thyristors (Stud Version), 1650 A



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	1	180° condu	ction, half sine v	wave	1650 (700)	Α
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	3080	
		t = 10 ms	No voltage		30 500	A kA <sup>2</sup> s
Maximum peak, one-cycle	<b>L</b>	t = 8.3 ms	reapplied		32 000	
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	Sinusoidal half wave, initial $T_J = T_J$ maximum	25 700	
		t = 8.3 ms	reapplied		26 900	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage reapplied		4651	
	l <sup>2</sup> t	t = 8.3 ms			4250	
		t = 10 ms			3300	
		t = 8.3 ms	reapplied		3000	
Maximum $I^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	t = 0.1 ms to	o 10 ms, no volt	tage reapplied	46 510	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.91	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			]
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			0.21	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.19	11152
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 4000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.73	V
Maximum holding current	I <sub>H</sub>	T _ 05 °C	anada aunnis 1	2 V registive lead	600	mA
Typical latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load		1000		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs		
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.9			
Typical turn-off time	t <sub>q</sub>	$I_{TM} = 550 \text{ A, } T_J = T_J \text{ maximum, dl/dt} = 40 \text{ A/}\mu\text{s,}$ $V_R = 50 \text{ V, dV/dt} = 20 \text{ V/}\mu\text{s, gate 0 V 100 }\Omega, t_p = 500 \mu\text{s}$	200	μs		

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs	
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA	



### Phase Control Thyristors (Stud Version), 1650 A

# Vishay High Power Products

TRIGGERING						
PARAMETER	SYMBOL		TEST COMPLETIONS		VALUES	
PARAMETER	STWIDOL	15	ST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	1	6	W
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	;	3	\ \v
Maximum peak positive gate current	I <sub>GM</sub>			3	.0	Α
Maximum peak positive gate voltage	+ V <sub>GM</sub>	$T_J = T_J$ maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms			V
Maximum peak negative gate voltage	- V <sub>GM</sub>		5.0			
DC gate current required to trigger		T <sub>J</sub> = - 40 °C	Maximum required gate trigger/current/voltage are the lowest	200	-	mA
	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		100	200	
		T <sub>J</sub> = 125 °C		50	-	
		T <sub>J</sub> = - 40 °C	value which will trigger all units	1.4	-	
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.1	3.0	V
		T <sub>J</sub> = 125 °C		0.9	-	
DC gate current not to trigger	I <sub>GD</sub>	T. T. massimum	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J \text{ maximum}$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		- 40 to 125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		- 40 to 150		
Maximum thermal resistance,	В	DC operation single side cooled	0.0.42	K/W	
junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.021		
Maximum thermal resistance,		DC operation single side cooled	0.006	N/ VV	
case to heatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.003		
Mounting force, ± 10 %			24 500 (2500)	N (kg)	
Approximate weight			425	g	
Case style		See dimensions - link at the end of datasheet A-24 (K-PUK)		(-PUK)	

△R <sub>thJC</sub> CONDUCTION								
CONDUCTION ANGLE	SINUSOIDAL	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		UNITS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS		
180°	0.003	0.003	0.002	0.002				
120°	0.004	0.004	0.004	0.004	$T_J = T_J$ maximum	K/W		
90°	0.005	0.005	0.005	0.005				
60°	0.007	0.007	0.007	0.007				
30°	0.012	0.012	0.012	0.012				

#### Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

### Vishay High Power Products

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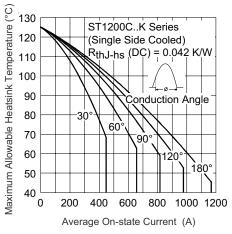


Fig. 1 - Current Ratings Characteristics

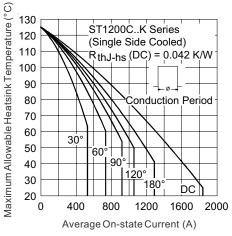


Fig. 2 - Current Ratings Characteristics

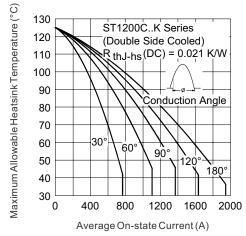


Fig. 3 - Current Ratings Characteristics

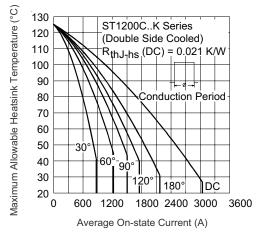


Fig. 4 - Current Ratings Characteristics

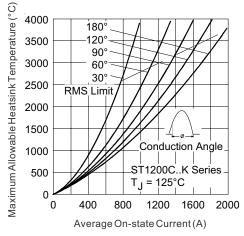


Fig. 5 - On-State Power Loss Characteristics

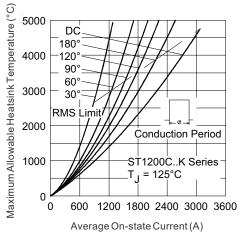


Fig. 6 - On-State Power Loss Characteristics



# Phase Control Thyristors (Stud Version), 1650 A

## Vishay High Power Products

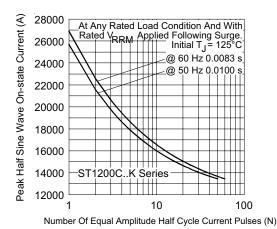


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

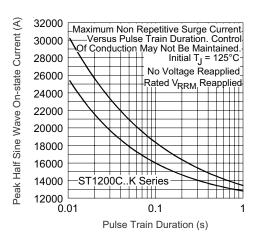


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

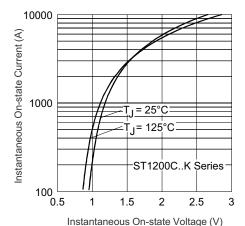


Fig. 9 - On-State Voltage Drop Characteristics

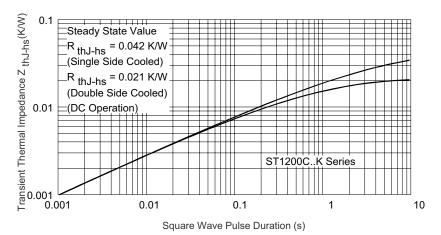


Fig. 10 - Thermal Impedance Z<sub>thJ-hs</sub> Characteristics

### Vishay High Power Products

# Phase Control Thyristors (Stud Version), 1650 A



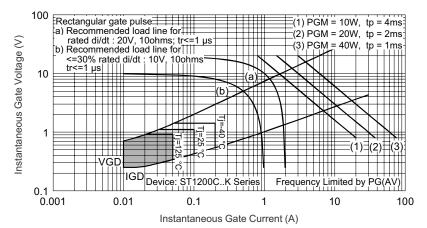
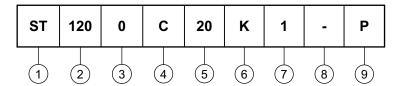


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



- 1 Thyristor
- 2 Essential part number
- 3 0 = Converter grade
- 4 C = Ceramic PUK
- 5 Voltage code: Code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)
- 6 K = PUK case A-24 (K-PUK)
- 7 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)
  - 1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)
  - 2 = Eyelet terminals (gate and auxiliary cathode soldered leads)
  - 3 = Fast-on terminals (gate and auxiliary cathode soldered leads)
- 8 Critical dV/dt: None = 500 V/µs (standard selection)
  - L = 1000 V/µs (special selection)
- 9 P = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			

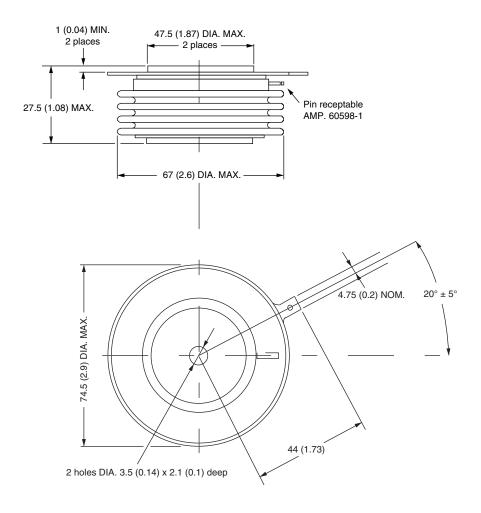
Document Number: 94394 Revision: 23-Apr-10

## Vishay Semiconductors

## A-24 (K-PUK)

### **DIMENSIONS** in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)





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